

Docket No.: 242984US2CIP

OBLON
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P.C.

COMMISSIONER FOR PATENTS ALEXANDRIA, VIRGINIA 22313

ATTORNEYS AT LAW

RE: Application Serial No.: 10/670,331

Applicants: Mitsuru KANEDA, et al. Filing Date: September 26, 2003

For: SEMICONDUCTOR SUBSTRATE WITH DEFECTS

REDUCED OR REMOVED AND METHOD OF

MANUFACTURING THE SAME, AND SEMICONDUCTOR DEVICE CAPABLE OF

BIDIRECTIONALLY RETAINING BREAKDOWN VOLTAGE AND METHOD OF MANUFACTURING

THE SAME

Group Art Unit: 2825

Examiner: KESHAVAN, B. V.

SIR:

Attached hereto for filing are the following papers:

## **RESPONSE**

Our check in the amount of \$0.00 is attached covering any required fees. In the event any variance exists between the amount enclosed and the Patent Office charges for filing the above-noted documents, including any fees required under 37 C.F.R 1.136 for any necessary Extension of Time to make the filing of the attached documents timely, please charge or credit the difference to our Deposit Account No. 15-0030. Further, if these papers are not considered timely filed, then a petition is hereby made under 37 C.F.R. 1.136 for the necessary extension of time. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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## IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF

MITSURU KANEDA, ET AL. : EXAMINER: KESHAVAN, B. V.

SERIAL NO: 10/670,331

FILED: SEPTEMBER 26, 2003 : GROUP ART UNIT: 2825

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## **RESPONSE**

COMMISSIONER FOR PATENTS ALEXANDRIA, VIRGINIA 22313

SIR:

**SAME** 

In response to the Office Action dated June 17, 2004, please consider the aboveidentified application as follows:

Remarks/Arguments begin on page 2 of this paper.